

# SCT2280KE

### **N-channel SiC power MOSFET**

$V_{DSS}$	1200V
R <sub>DS(on)</sub> (Typ.)	280mΩ
I <sub>D</sub>	14A
$P_{D}$	108W

1) Low on-resistance

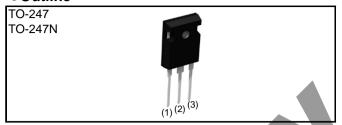
Features

- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

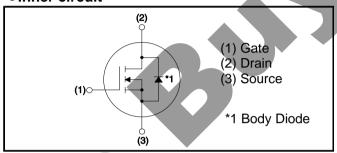
### Application

- Solar inverters
- DC/DC converters
- · Induction heating
- Motor drives

### Outline



### •Inner circuit



### ● Packaging specifications\*1

	Packa	age	TO-247	TO-247N		
	Packing	Tube				
		Reel size (mm)	-			
ı	Typo	Tape width (mm)	-			
	Туре	Basic ordering unit (pcs) Packing code		0		
				C11		
		Marking	SCT2	280KE		

### • Absolute maximum ratings $(T_a = 25^{\circ}C)$

Parameter	Symbol	Value	Unit	
Drain - Source voltage	$V_{DSS}$	1200	V	
Continuous drain current	$T_c = 25^{\circ}C$	I <sub>D</sub> *2	14	А
Continuous diami current	T <sub>c</sub> = 100°C	l <sub>D</sub> *2	10	А
Pulsed drain current		I <sub>D,pulse</sub> *3	35	Α
Gate - Source voltage (DC)		$V_{GSS}$	−6 to 22	V
Gate - Source surge voltage (T <sub>surge</sub> < 300nsec)		V <sub>GSS-surge</sub> *4	−10 to 26	V
Power dissipation (T <sub>c</sub> = 25°C)		P <sub>D</sub>	108	W
Junction temperature		T <sub>j</sub>	175	°C
Range of storage temperature		T <sub>stg</sub>	-55 to +175	°C

# • Electrical characteristics $(T_a = 25^{\circ}C)$

Parameter	Symbol	Conditions		Unit			
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	UTIIL	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	1200	,	-	V	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = 1200V, V_{GS} = 0V$ $T_{j} = 25^{\circ}C$ $T_{j} = 150^{\circ}C$	1 1	1 2	10	μА	
Gate - Source leakage current	$I_{GSS+}$	$V_{GS} = +22V, V_{DS} = 0V$	1		100	nA	
Gate - Source leakage current	I <sub>GSS</sub> _	$V_{GS} = -6V, V_{DS} = 0V$	-		-100	nA	
Gate threshold voltage	V <sub>GS (th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 1.4 \text{mA}$	1.6	2.8	4.0	V	

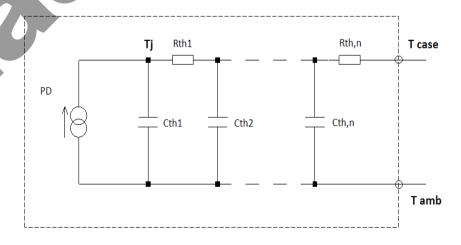
### ●Thermal resistance

Parameter	Symbol	Values			Unit
- Farameter	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R <sub>thJC</sub>	-	1.07	1.39	°C/W
Thermal resistance, junction - ambient	$R_{thJA}$	-	ı	50	°C/W
Soldering temperature, wavesoldering for 10s	T <sub>sold</sub>	-	-	265	°C

# ●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R <sub>th1</sub>	1.00E-01	
R <sub>th2</sub>	6.62E-01	K/W
R <sub>th3</sub>	3.04E-01	

Symbol	Value	Unit
C <sub>th1</sub>	8.61E-04	
C <sub>th2</sub>	2.84E-03	Ws/K
C <sub>th3</sub>	5.59E-02	



# ●Electrical characteristics (T<sub>a</sub> = 25°C)

Doromotor	Cymahal	Conditions	Values			Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic	
		$V_{GS} = 18V, I_{D} = 4A$					
Static drain - source on - state resistance	R <sub>DS(on)</sub> *5	T <sub>j</sub> = 25°C	-	280	364	mΩ	
		T <sub>j</sub> = 125°C	-	388	-		
Gate input resistance	$R_{G}$	f = 1MHz, open drain	-	17		Ω	
Transconductance	<b>g</b> fs *5	$V_{DS} = 10V, I_D = 4A$	-	1.4	1	S	
Input capacitance	C <sub>iss</sub>	$V_{GS} = 0V$	-	667			
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 800V	-	27	-	pF	
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	5	-		
Effective output capacitance, energy related	C <sub>o(er)</sub>	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V		41	-	pF	
Turn - on delay time	t <sub>d(on)</sub> *5	$V_{DD} = 400V, V_{GS} = 18V$		19	-		
Rise time	t <sub>r</sub> *5	$I_D = 4A$	-	19	-		
Turn - off delay time	t <sub>d(off)</sub> *5	$R_L = 100\Omega$	-	47	-	ns	
Fall time	t <sub>f</sub> *5	$R_G = 0\Omega$	-	29	-		
Turn - on switching loss	E <sub>on</sub> *5	$V_{DD} = 600V, I_{D} = 4A$ $V_{GS} = 18V/0V$	-	57	-	1	
Turn - off switching loss	E <sub>off</sub> *5	$R_G = 0Ω$ , L=500µH *E <sub>on</sub> includes diode reverse recovery	-	20	-	μJ	

### ● Gate Charge characteristics (T<sub>a</sub> = 25°C)

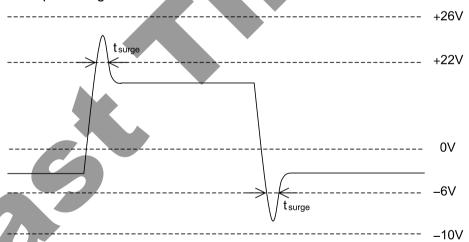
Parameter	Symbol	Conditions -	Values			Unit
Parameter	Symbol		Min.	Тур.	Max.	Offic
Total gate charge	$Q_g^{*5}$	V <sub>DD</sub> = 400V	-	36	-	
Gate - Source charge	Q <sub>gs</sub> *5	I <sub>D</sub> = 4A	-	9	-	nC
Gate - Drain charge	Q <sub>gd</sub> *5	V <sub>GS</sub> = 18V	-	12	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} = 400V, I_D = 4A$	-	9.8	-	V

### ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Cymbol	Conditions		Unit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l <sub>S</sub> *2	-T <sub>c</sub> = 25°C	-	-	14	A
Inverse diode direct current, pulsed	I <sub>SM</sub> *3		-	-	35	A
Forward voltage	V <sub>SD</sub> *5	$V_{GS} = 0V$ , $I_S = 4A$	-	4.0	7	V
Reverse recovery time	t <sub>rr</sub> *5		-	22		ns
Reverse recovery charge	Q <sub>rr</sub> *5	I <sub>F</sub> = 4A, V <sub>R</sub> = 400V di/dt = 160A/μs	-	21		nC
Peak reverse recovery current	I <sub>rrm</sub> *5		-	2.0	-	Α

<sup>\*1</sup> Tolerances of dimensions and packing specifications slightly differ between TO-247 and TO-247N, which is unlikely to influence compatibility for mounting. Please refer to corresponding specifications of dimensions for more details.

<sup>\*4</sup> Example of acceptable Vgs waveform



4 Pulsed

<sup>\*2</sup> Limited only by maximum temperature allowed.

<sup>\*3</sup> PW  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

Fig.1 Power Dissipation Derating Curve

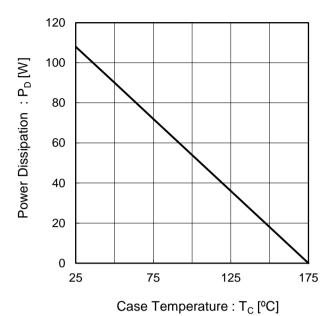


Fig.2 Maximum Safe Operating Area

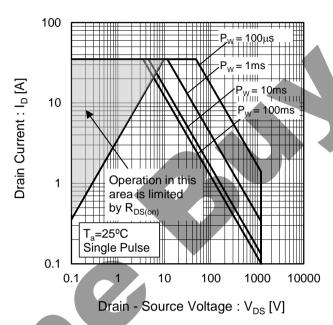


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width

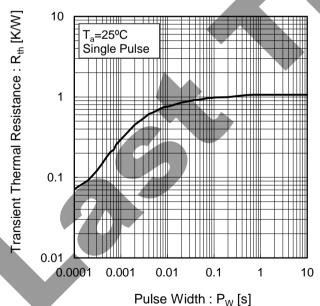


Fig.4 Typical Output Characteristics(I)

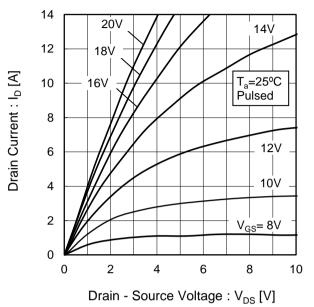
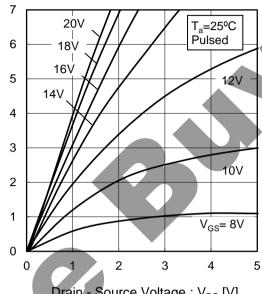
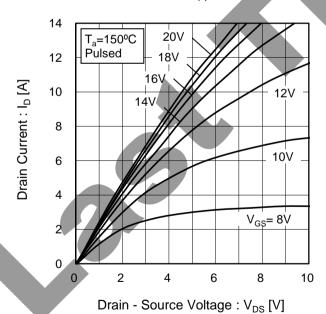


Fig.5 Typical Output Characteristics(II)



Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.6 T<sub>i</sub> = 150°C Typical Output Characteristics(I)



Drain Current : I<sub>D</sub> [A]

0

Drain Current: I<sub>D</sub> [A]

7 20V T<sub>a</sub>=150°C Pulsed 6 18V 2V 16V 5 10V 4 3  $V_{GS} = 8V$ 2 1 0

Fig.7 T<sub>j</sub> = 150°C Typical Output Characteristics(II)

Drain - Source Voltage: V<sub>DS</sub> [V]

3

2

5

Fig.8 Typical Transfer Characteristics (I)

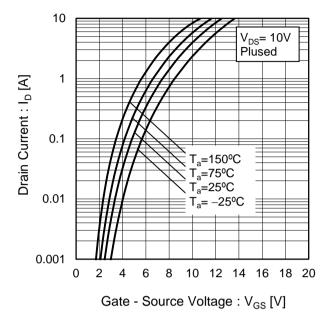


Fig.9 Typical Transfer Characteristics (II)

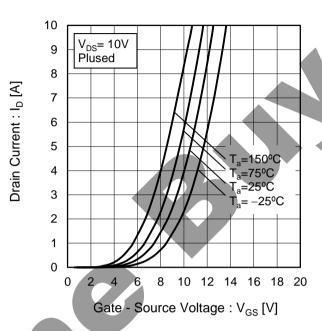


Fig.10 Gate Threshold Voltage vs. Junction Temperature

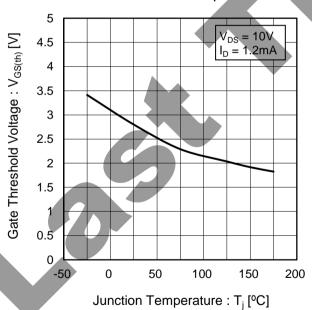


Fig.11 Transconductance vs. Drain Current

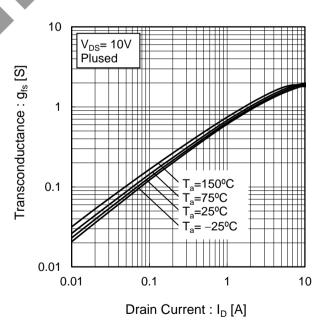


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

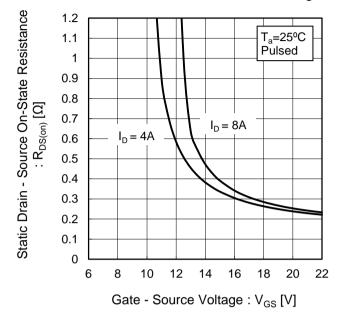


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

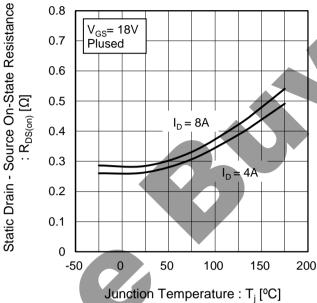


Fig.14 Static Drain - Source On - State
Resistance vs. Drain Current

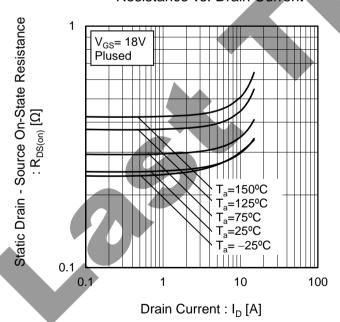
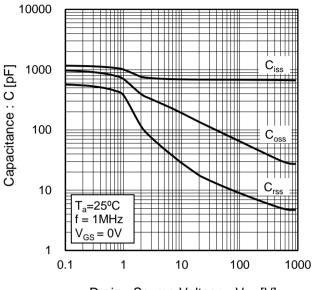


Fig.15 Typical Capacitance vs. Drain - Source Voltage



Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.16 C<sub>OSS</sub> Stored Energy

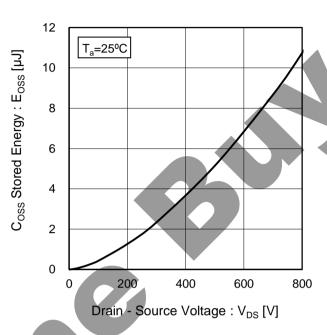


Fig.17 Switching Characteristics

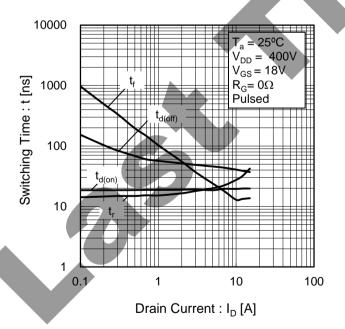
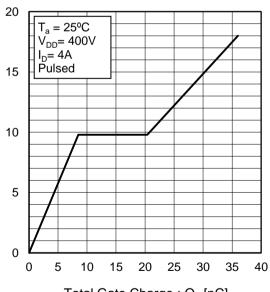


Fig.18 Dynamic Input Characteristics



Total Gate Charge : Q<sub>q</sub> [nC]

Gate - Source Voltage :  $\mathsf{V}_{\mathsf{GS}}\left[\mathsf{V}
ight]$ 

Fig.19 Typical Switching Loss vs. Drain - Source Voltage

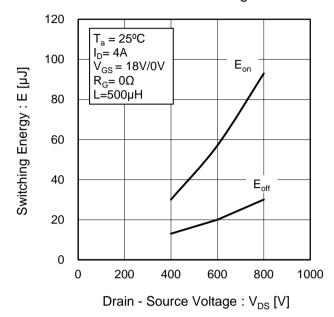


Fig.20 Typical Switching Loss vs. Drain Current

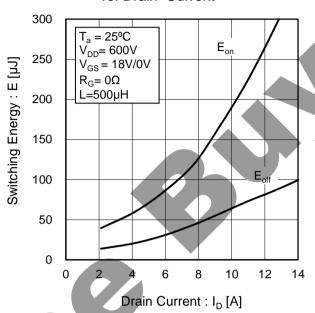


Fig.21 Typical Switching Loss vs. External Gate Resistance

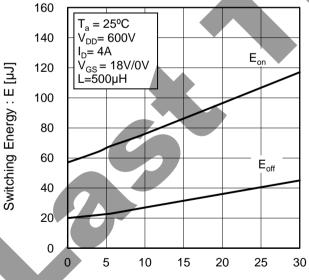


Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

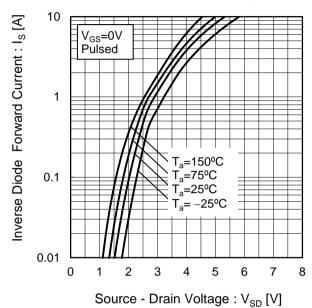
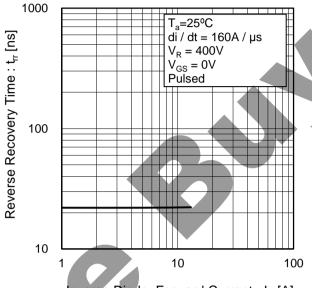


Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I<sub>S</sub> [A]



### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

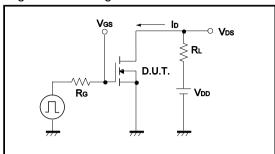


Fig.2-1 Gate Charge Measurement Circuit

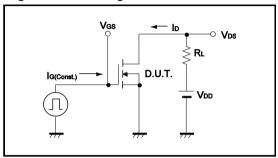


Fig.3-1 Switching Energy Measurement Circuit

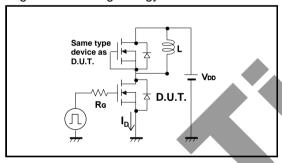


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

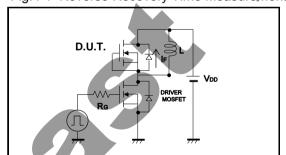


Fig.1-2 Switching Waveforms

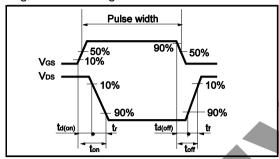


Fig.2-2 Gate Charge Waveform

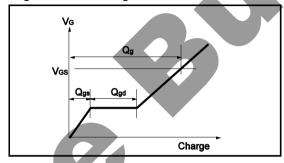
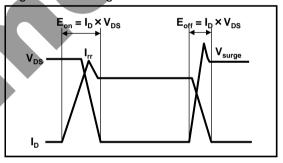
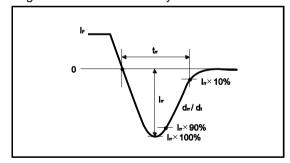


Fig.3-2 Switching Waveforms





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